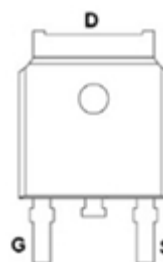
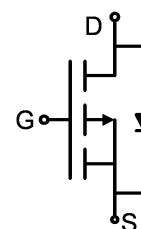


Main Product Characteristics:

V_{DS}	-40V
$R_{DS(on)}$	24mohm(typ.)
I_D	-30A


TO-252

**Marking and pin
Assignment**

Schematic diagram
Features and Benefits:

- Advanced MOSFET process technology
- Special designed for PWM, load switching and general purpose applications
- Ultra low on-resistance with low gate charge
- Fast switching and reverse body recovery
- 100% Avalanche Rated


Description:

It utilizes the latest trench processing techniques to achieve the high cell density and reduces the on-resistance with high repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in power switching application and a wide variety of other applications

Absolute max Rating:

Symbol	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	-30①	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	-20①	
I_{DM}	Pulsed Drain Current ②	-120	
$P_D @ T_C = 25^\circ\text{C}$	Power Dissipation ③	83	W
	Linear Derating Factor	1.02	W/°C
V_{DS}	Drain-Source Voltage	-40	V
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy @ $L=0.3\text{mH}$	93	mJ
I_{AS}	Avalanche Current @ $L=0.3\text{mH}$	25	A
T_J	Operating Junction Temperature Range	-55 to + 150	°C
T_{STG}	Storage Temperature Range		

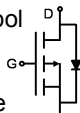
Thermal Resistance

Symbol	Characterizes	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-case ③	—	1.5	°C/W
$R_{\theta JA}$	Junction-to-ambient ($t \leq 10s$) ④	—	62	°C/W
	Junction-to-Ambient (PCB mounted, steady-state) ④	—	40	°C/W

Electrical Characterizes @ $T_A=25^\circ\text{C}$ unless otherwise specified

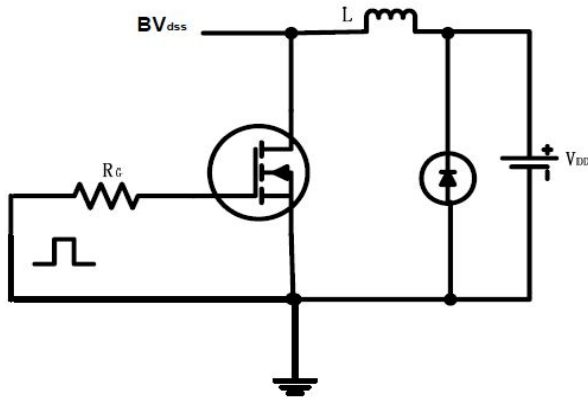
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source breakdown voltage	-40	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
$R_{DS(on)}$	Static Drain-to-Source on-resistance	—	24	32	mΩ	$V_{GS}=-10V, I_D = -10A$
		—	33	45		$V_{GS}=-4.5V, I_D = -6A$
$V_{GS(th)}$	Gate threshold voltage	-1	—	-3	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
I_{DSS}	Drain-to-Source leakage current	—	—	-1	μA	$V_{DS} = -40V, V_{GS} = 0V$ $T_J = 125^\circ\text{C}$
		—	—	-50		
I_{GSS}	Gate-to-Source forward leakage	—	—	100	nA	$V_{GS} = 20V$
		—	—	-100		$V_{GS} = -20V$
Q_g	Total gate charge	—	26.2	—	nC	$I_D = -10A,$ $V_{DS}=-20V,$ $V_{GS} = -10V$
Q_{gs}	Gate-to-Source charge	—	7.2	—		
Q_{gd}	Gate-to-Drain("Miller") charge	—	8.4	—		
$t_{d(on)}$	Turn-on delay time	—	15.9	—	nS	$V_{GS}=-10V, V_{DS} = -20V,$ $R_L=1\Omega,$ $R_{GEN}=3\Omega$ $I_D = -20A$
t_r	Rise time	—	49.0	—		
$t_{d(off)}$	Turn-Off delay time	—	61.6	—		
t_f	Fall time	—	25.6	—		
C_{iss}	Input capacitance	—	1820	—	pF	$V_{GS} = 0V$
C_{oss}	Output capacitance	—	248	—		$V_{DS} = -25V$
C_{rss}	Reverse transfer capacitance	—	162	—		$f = 1MHz$

Source-Drain Ratings and Characteristics

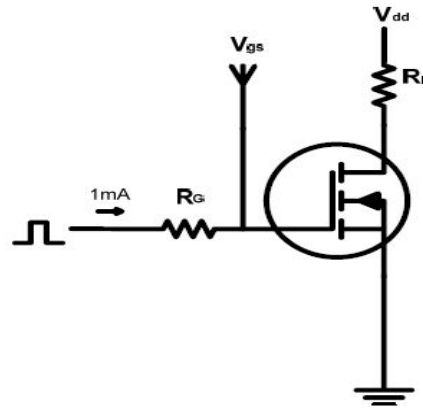
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-30①	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode)	—	—	-120	A	
V_{SD}	Diode Forward Voltage	—	-0.72	-1.2	V	$I_S=-2.1A, V_{GS}=0V$
t_{rr}	Reverse Recovery Time	—	30.8	—	nS	$T_J = 25^\circ\text{C}, I_F = -20A, di/dt = 100A/\mu s$
Q_{rr}	Reverse Recovery Charge	—	31.1	—	nC	

Test circuits and Waveforms

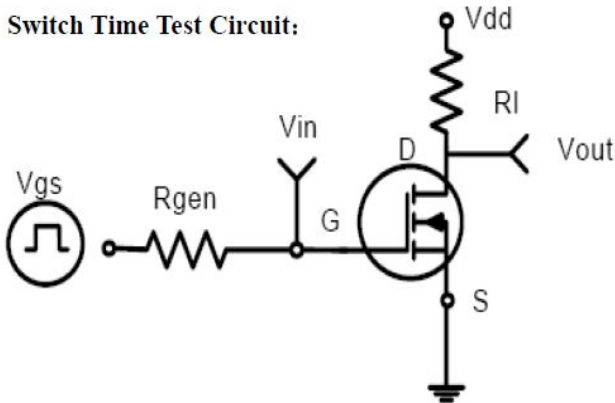
EAS test circuits:



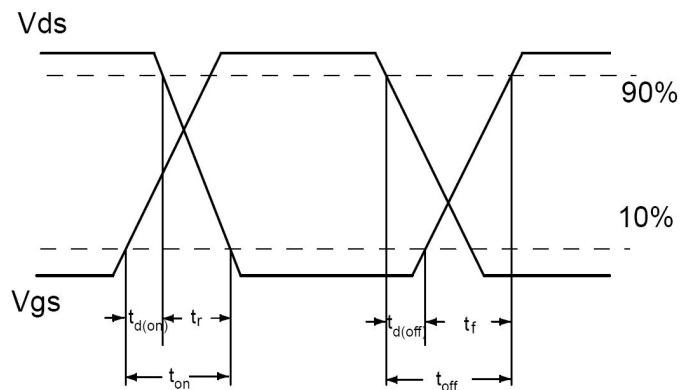
Gate charge test circuit:



Switch Time Test Circuit:

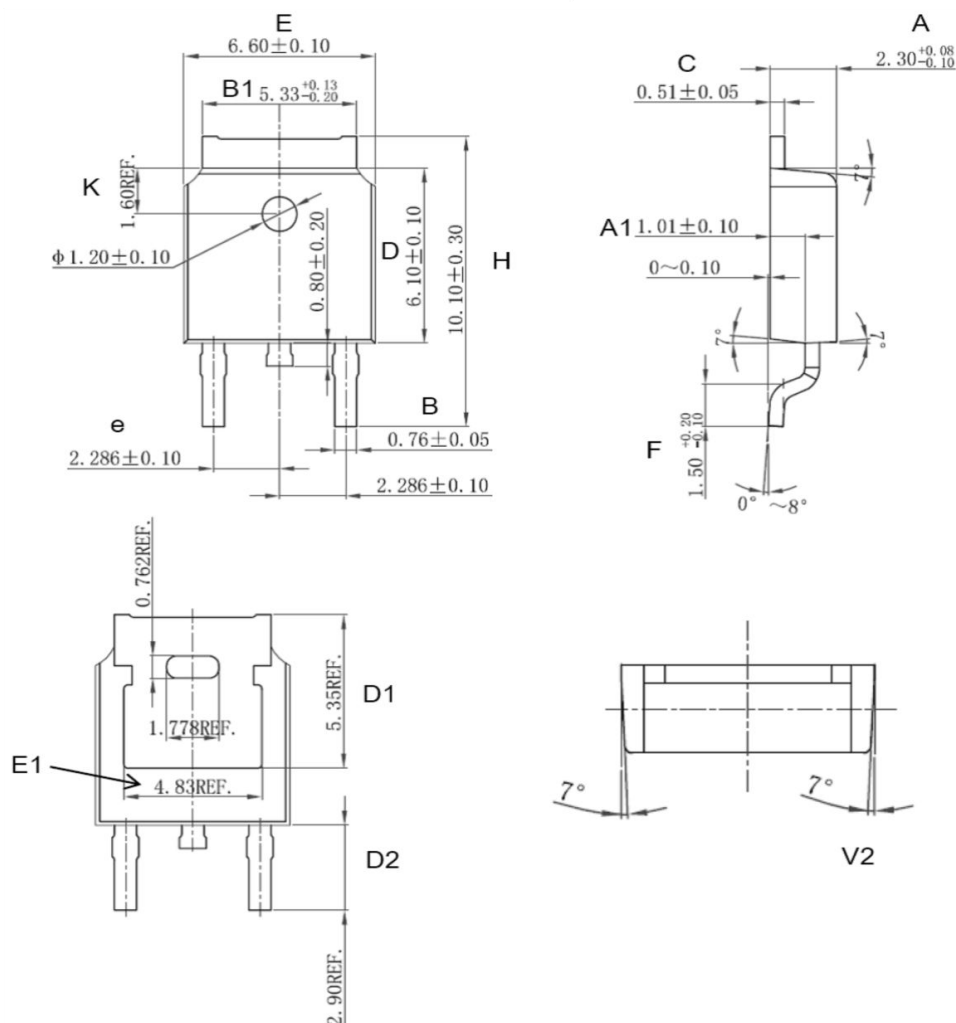


Switch Waveforms:



Notes:

- ① Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 75A.
- ② Repetitive rating; pulse width limited by max. junction temperature.
- ③ The power dissipation PD is based on max. junction temperature, using junction-to-case thermal resistance.
- ④ The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.
- ⑤ These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)} = 175^\circ\text{C}$.

Mechanical Data:
DPAK PACKAGE OUTLINE DIMENSION


Symbol	Dimension In Millimeters			Dimension In Inches		
	Min	Nom	Max	Min	Nom	Max
A	2.200	2.300	2.380	0.087	0.091	0.094
A1	0.910	1.010	1.110	0.036	0.040	0.044
B	0.710	0.760	0.810	0.028	0.030	0.032
B1	5.130	5.330	5.460	0.202	0.210	0.215
C	0.460	0.510	0.560	0.018	0.020	0.022
D	6.000	6.100	6.200	0.236	0.240	0.244
D1	5.350 (REF)			0.211 (REF)		
D2	2.900 (REF)			0.114 (REF)		
E	6.500	6.600	6.700	0.256	0.260	0.264
E1	4.83 (REF)			0.190 (REF)		
e	2.186	2.286	2.386	0.086	0.090	0.094
H	9.800	10.100	10.400	0.386	0.398	0.409
F	1.400	1.500	1.700	0.055	0.059	0.067
K	1.600 (REF)			0.063 (REF)		
V2	8° (REF)			8° (REF)		

Ordering and Marking Information

Device Marking: SSF4031C1

Package (Available)
DPAK (TO-252)
Operating Temperature Range
C : -55 to 150 °C

Devices per Unit

Option1:

Package Type	Units/Tape	Tapes/Inner Box	Units/Inner Box	Inner Boxes/Carton Box	Units/Carton Box
TO-252	2500	2	5000	7	35000

Option2:

Package Type	Units/Tape	Tapes/Inner Box	Units/Inner Box	Inner Boxes/Carton Box	Units/Carton Box
TO-252	2500	1	2500	10	25000

Reliability Test Program

Test Item	Conditions	Duration	Sample Size
High Temperature Reverse Bias(HTRB)	T _j =125°C to 150°C @ 80% of Max V _{DSS} /V _{CES} /V _R	168 hours 500 hours 1000 hours	3 lots x 77 devices
High Temperature Gate Bias(HTGB)	T _j =150°C @ 100% of Max V _{GSS}	168 hours 500 hours 1000 hours	3 lots x 77 devices

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